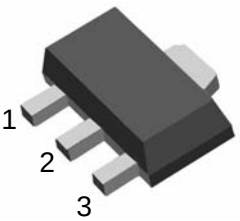
Transys Electronics LIMITED

SOT-89 Plastic-Encapsulated Transistors

2SA1213 TRANSISTOR (PNP)

SOT-89

1. BASE
2. COLLECTO 1
3. EMITTER



FEATURES

Power dissipation

P_{CM} : 0.5 W (Tamb=25℃)

Collector current

I_{CM} : -2 A

Collector-base voltage

$V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-100μA , I_E=0	-50		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -10mA , I_B=0	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-50 V , I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5 V , I_C=0		-0.1	μA
DC current gain	$h_{FE\ 1}$	V_{CE}=-2V, I_C= -0.5A	70	240	
	$h_{FE\ 2}$	V_{CE}=-2V, I_C= -2A	20		
Collector-emitter saturation voltage	V_{CEsat}	I_C=-1A, I_B= -0.05A		-0.5	V
Base-emitter saturation voltage	V_{BEsat}	I_C=-1A, I_B= -0.05A		-1.2	V
Transition frequency	f_T	V_{CE}= -2V, I_C=-0.5A	100		MHz

CLASSIFICATION OF h_{FE}

Rank	**O**	**Y**
Range	70-140	120-240

Marking	NO,NY